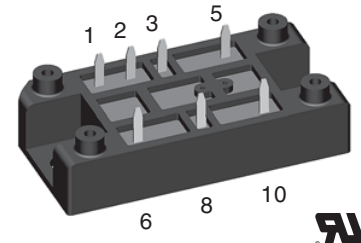
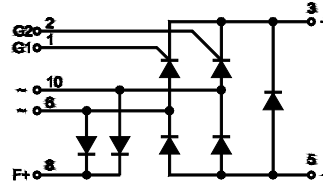


Half Controlled Single Phase Rectifier Bridge

Including Freewheeling Diode and Field Diodes

$V_{RRM} = 800-1600\text{ V}$
 $I_{dAVM} = 32\text{ A}$

V_{RSM}	V_{RRM}	Type
V_{DSM}	V_{DRM}	
V	V	
900	800	VHFD 29-08io1
1300	1200	VHFD 29-12io1
1700	1600	VHFD 29-16io1



Bridge and Freewheeling Diode

Symbol	Conditions	Maximum Ratings	
I_{dAV}	$T_H = 85^\circ\text{C}$, module	28	A
I_{dAVM}^*	module	32	A
I_{FRMS}, I_{TRMS}	per leg	25	A
I_{FSM}, I_{TSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0\text{ V}$	$t = 10\text{ ms}$ (50 Hz), sine	300 A
		$t = 8.3\text{ ms}$ (60 Hz), sine	330 A
I^2t	$T_{VJ} = T_{VJM}$ $V_R = 0\text{ V}$	$t = 10\text{ ms}$ (50 Hz), sine	270 A
		$t = 8.3\text{ ms}$ (60 Hz), sine	300 A
$(di/dt)_{cr}$	$T_{VJ} = 125^\circ\text{C}$ $f = 50\text{ Hz}$, $t_p = 200\text{ }\mu\text{s}$ $V_D = 2/3 V_{DRM}$	repetitive, $I_T = 50\text{ A}$	150 A/ μs
	$I_G = 0.3\text{ A}$, $di_G/dt = 0.3\text{ A}/\mu\text{s}$	non repetitive, $I_T = 0.5 I_{dAV}$	500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{(vj)m}$; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	1000	V/ μs
V_{RGM}		10	V
P_{GM}	$T_{VJ} = T_{VJM}$	$t_p = 30\text{ }\mu\text{s}$	$\leq 10\text{ W}$
	$I_T = 0.5 I_{dAVM}$	$t_p = 500\text{ }\mu\text{s}$	$\leq 5\text{ W}$
		$t_p = 10\text{ ms}$	$\leq 1\text{ W}$
P_{GAVM}		0.5	W
T_{VJ}		-40...+125	$^\circ\text{C}$
T_{VJM}		125	$^\circ\text{C}$
T_{stg}		-40...+125	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS	$t = 1\text{ min}$	3000 V~
	$I_{ISOL} \leq 1\text{ mA}$	$t = 1\text{ s}$	3600 V~
d_s	Creep distance on surface	12.7	mm
d_A	Strike distance in air	9.4	mm
a	Max. allowable acceleration	50	m/s ²
M_d	Mounting torque (M5) (10-32 UNF)	2-2.5	Nm
		18-22	lb.in.
Weight		35	g

Features

- Package with DCB ceramic base plate
- Isolation voltage 3600 V~
- Planar passivated chips
- Blocking voltage up to 1600 V
- Low forward voltage drop
- Leads suitable for PC board soldering
- UL registered E 72873

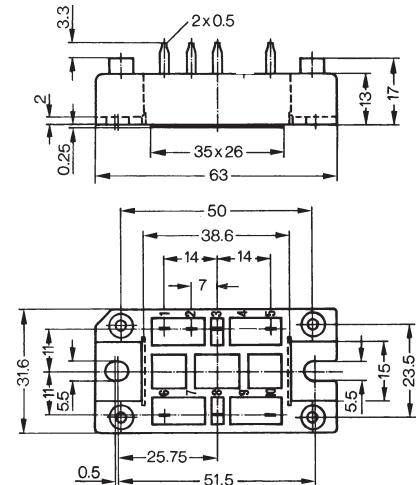
Applications

- Supply for DC power equipment
- DC motor control

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

Dimensions in mm (1 mm = 0.0394")



Symbol	Conditions	Characteristic Values
I_R, I_D	$V_R = V_{RRM}; V_D = V_{DRM}$ $T_{VJ} = T_{VJM}$ $T_{VJ} = 25^\circ\text{C}$	≤ 5 mA ≤ 0.3 mA
V_T, V_F	$I_T, I_F = 45$ A; $T_{VJ} = 25^\circ\text{C}$	≤ 1.6 V
V_{T0}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)	0.9 V
r_T		15 m Ω
V_{GT}	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	≤ 1.0 V ≤ 1.2 V
I_{GT}	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	≤ 65 mA ≤ 80 mA ≤ 50 mA
V_{GD}	$T_{VJ} = T_{VJM};$ $V_D = 2/3 V_{DRM}$	≤ 0.2 V
I_{GD}	$T_{VJ} = T_{VJM};$ $V_D = 2/3 V_{DRM}$	≤ 5 mA
I_L	$I_G = 0.3$ A; $t_G = 30$ μs ; $di_G/dt = 0.3$ A/ μs ; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	≤ 150 mA ≤ 200 mA ≤ 100 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6$ V; $R_{GK} = \infty$	≤ 100 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 0.5 V_{DRM}$ $I_G = 0.3$ A; $di_G/dt = 0.3$ A/ μs	≤ 2 μs
t_q	$T_{VJ} = 125^\circ\text{C}; I_T = 15$ A; $t_p = 300$ μs ; $V_R = 100$ V	typ. 150 μs
Q_f	$di/dt = -10$ A/ μs ; $dv/dt = 20$ V/ μs ; $V_D = 2/3 V_{DRM}$	75 μC
R_{thJC}	per thyristor (diode); DC current	1.4 K/W
	per module	0.35 K/W
R_{thJH}	per thyristor (diode); DC current	2.0 K/W
	per module	0.5 K/W

Field Diodes

Symbol	Conditions	Maximum Ratings
I_{FAV}	$T_H = 85^\circ\text{C}$, per Diode	4 A
I_{FAVM}	per diode	4 A
I_{FRMS}	per diode	6 A
I_{FSM}	$T_{VJ} = 45^\circ\text{C};$ $V_R = 0$ V	$t = 10$ ms (50 Hz), sine $t = 8.3$ ms (60 Hz), sine
	$T_{VJ} = T_{VJM}$ $V_R = 0$ V	$t = 10$ ms (50 Hz), sine $t = 8.3$ ms (60 Hz), sine
I^2t	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$ V	$t = 10$ ms (50 Hz), sine $t = 8.3$ ms (60 Hz), sine
	$T_{VJ} = T_{VJM}$ $V_R = 0$ V	$t = 10$ ms (50 Hz), sine $t = 8.3$ ms (60 Hz), sine
I_R	$V_R = V_{RRM}$ $T_{VJ} = T_{VJM}$ $T_{VJ} = 25^\circ\text{C}$	1 mA 0.15 mA
V_F	$I_F = 21$ A; $T_{VJ} = 25^\circ\text{C}$	1.83 V
V_{T0}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)	0.9 V
r_T		50 m Ω
R_{thJC}	per diode; DC current	4.4 K/W
R_{thJH}	per diode; DC current	5.2 K/W

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

* for resistive load

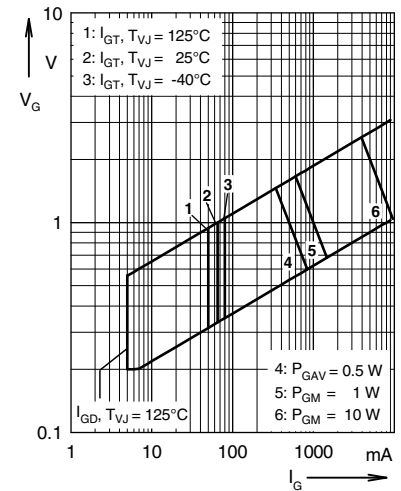


Fig. 1 Gate trigger range

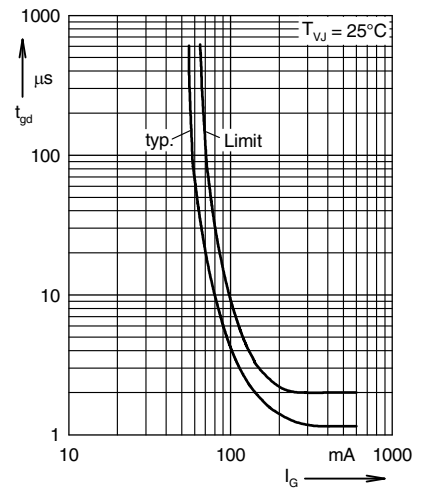


Fig. 2 Gate controlled delay time t_{gd}

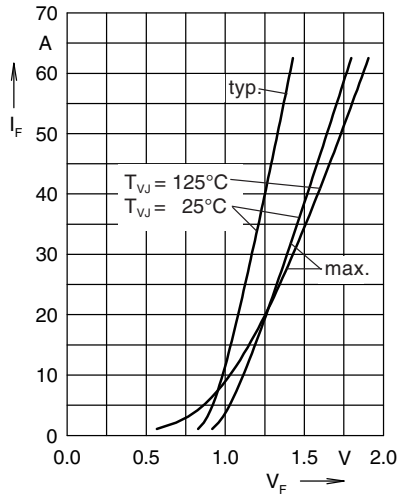


Fig. 3 Forward current vs. voltage drop per diode

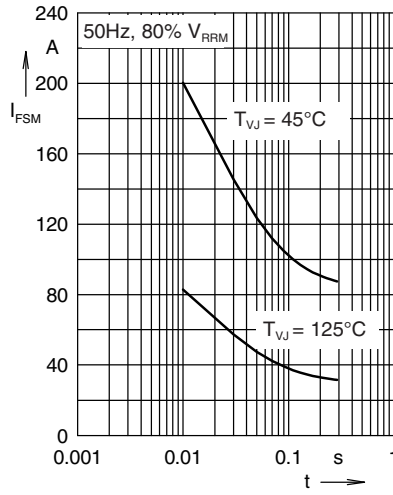


Fig. 4 Surge overload current

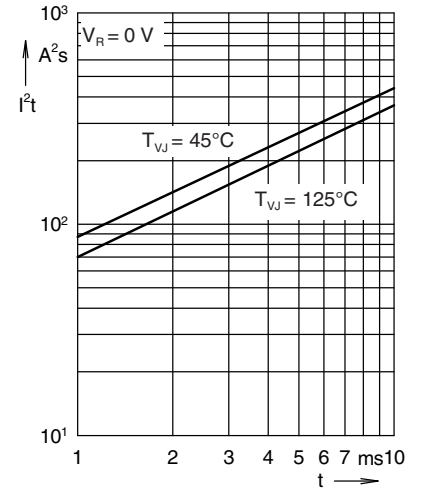


Fig. 5 I^2t versus time per diode

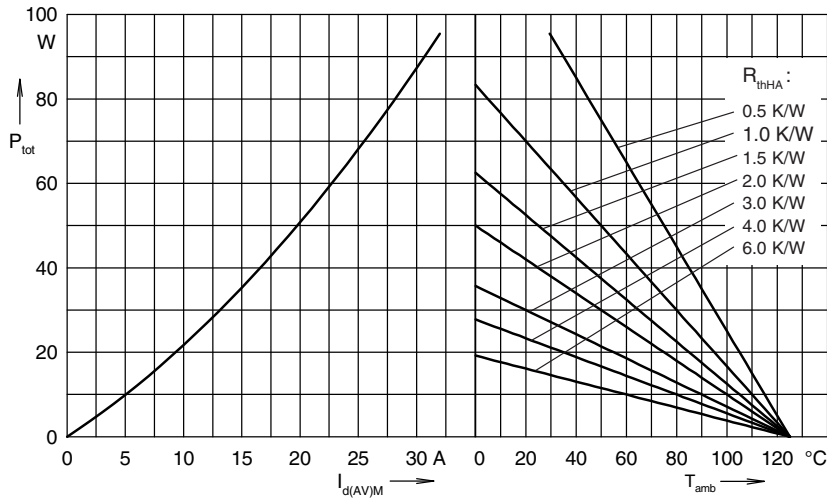


Fig. 6 Power dissipation vs. direct output current and ambient temperature

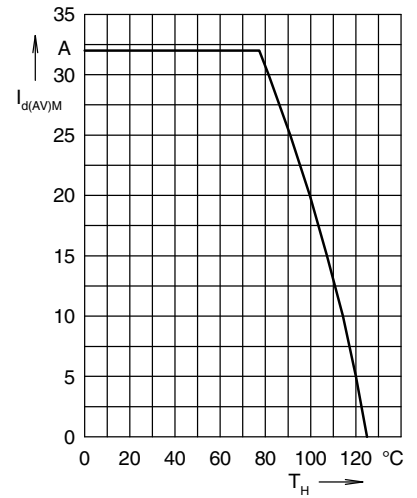


Fig. 7 Max. forward current vs. heatsink temperature

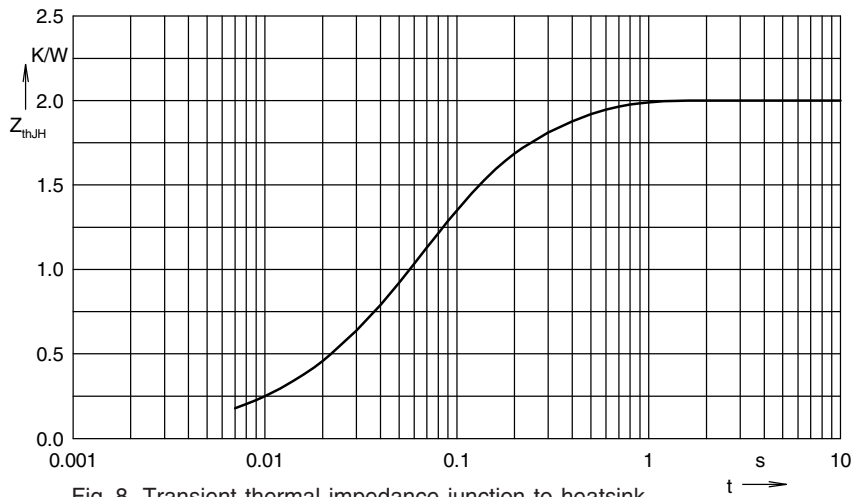


Fig. 8 Transient thermal impedance junction to heatsink

Constants for Z_{thJH} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.007	0.008
2	0.266	0.05
3	1.127	0.06
4	0.6	0.25